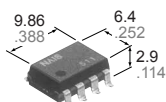
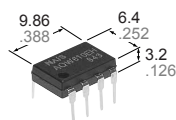


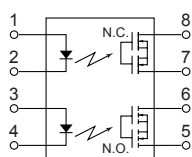
Panasonic
ideas for life

**General use and economy
type. DIP (1 Form A/1 Form B)
8-pin type.
Reinforced insulation
5,000V type.**

**GU-E PhotoMOS
(AQW610EH)**



mm inch



FEATURES

1. 60V type couples high capacity (0.5A) with low on-resistance (1Ω).

Item	GU-E (1 Form A/1 Form B type)	
	AQW610EH	AQW612EH
Part No.	AQW610EH	AQW612EH
Load voltage	350V	60V
Continuous load current	0.12A	0.5A
ON resistance (typ.)	18Ω	1Ω

2. This is the PhotoMOS 1 Form A/1 Form B output type relay that has attained a low, economical price.

3. Reinforced insulation 5,000 V type
More than 0.4 mm internal insulation distance between inputs and outputs. Conforms to EN41003, EN60950 (reinforced insulation).

4. Compact 8-pin DIP size
The device comes in a compact (W) 6.4×(L)9.86×(H)3.2 mm (W).252×(L).388×(H).126 inch, 8-pin DIP size (through hole terminal type).

5. Applicable for 1 Form A 1 Form B use as well as two independent 1 Form A and 1 Form B use

6. Controls low-level analog signals

PhotoMOS relays feature extremely low closed-circuit offset voltage to enable control of low-level analog signals without distortion.

7. High sensitivity, high speed response.

Can control a maximum 0.14 A load current with a 5 mA input current. Fast operation speed of 0.5ms (typ.) [N.O.]. (AQW610EH)

8. Low-level off-state leakage current

TYPICAL APPLICATIONS

- Power supply
- Measuring equipment
- Security equipment
- Modem
- Telephone equipment
- Electricity, plant equipment
- Sensors

TYPES

Type	I/O isolation voltage	Output rating*		Part No.				Packing quantity	
				Through hole terminal	Surface-mount terminal			Tube	Tape and reel
		Load voltage	Load current		Tube packing style		Tape and reel packing style		
AC/DC type	Reinforced 5,000 V	60 V	500 mA	AQW612EH	AQW612EHA	AQW612EHAX	AQW612EHAZ	1 tube contains 40 pcs. 1 batch contains 400 pcs.	1,000 pcs.
		350 V	120 mA	AQW610EH	AQW610EHA	AQW610EHAX	AQW610EHAZ		
		400 V	100 mA	AQW614EH	AQW614EHA	AQW614EHAX	AQW614EHAZ		

*Indicate the peak AC and DC values.

Note: For space reasons, the SMD terminal shape indicator "A" and the package type indicator "X" and "Z" are omitted from the seal.

GU-E PhotoMOS (AQW610EH)

RATING

1. Absolute maximum ratings (Ambient temperature: 25°C 77°F)

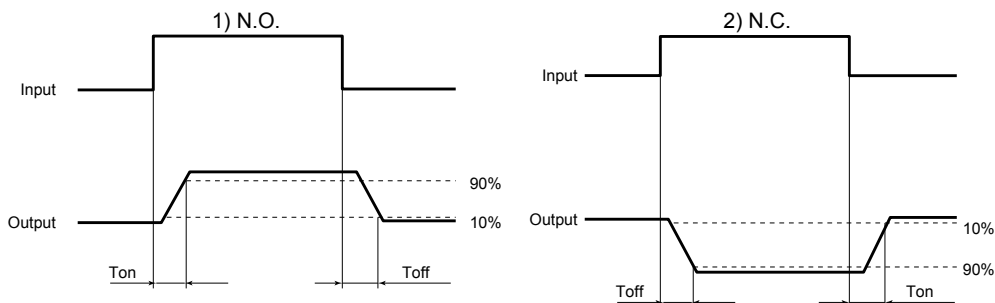
Item		Symbol	AQW612EH (A)	AQW610EH (A)	AQW614EH (A)	Remarks
Input	LED forward current	I_F	50 mA			
	LED reverse voltage	V_R	5 V			
	Peak forward current	I_{FP}	1 A			f = 100 Hz, Duty factor = 0.1%
	Power dissipation	P_{in}	75 mW			
Output	Load voltage (peak AC)	V_L	60 V	350 V	400 V	
	Continuous load current	I_L	0.5 A (0.6 A)	0.12 A (0.14 A)	0.1 A (0.13 A)	Peak AC, DC (): in case of using only 1a or 1b, 1 channel
	Peak load current	I_{peak}	1.5 A	0.36 A	0.3 A	100 ms (1 shot), $V_L = DC$
	Power dissipation	P_{out}	800 mW			
Total power dissipation		P_T	850 mW			
I/O isolation voltage		V_{iso}	5,000 V AC			
Temperature limits	Operating	T_{opr}	-40°C to +85°C -40°F to +185°F			Non-condensing at low temperatures
	Storage	T_{stg}	-40°C to +100°C -40°F to +212°F			

2. Electrical characteristics (Ambient temperature: 25°C 77°F)

Item		Symbol	AQW612EH (A)	AQW610EH (A)	AQW614EH (A)	Condition	
Input	LED operate current	Typical	$I_{Fon(N.O.)}$	1.3 mA		$I_L = Max.$	
		Maximum	$I_{Foff(N.C.)}$	3.0 mA			
	LED reverse current	Minimum	$I_{Foff(N.O.)}$	0.4 mA		$I_L = Max.$	
		Typical	$I_{Fon(N.C.)}$	1.3 mA			
LED dropout voltage	Typical	V_F	1.25 (1.14 V at $I_F = 5$ mA)			$I_F = 50$ mA	
	Maximum		1.5 V				
Output	On resistance	Typical	R_{on}	1Ω	18Ω	26Ω	$I_F = 5$ mA (N.O.) $I_F = 0$ mA (N.C.) $I_L = Max.$ Within 1 s on time
		Maximum		2.5Ω	25Ω	35Ω	
	Off state leakage current	Maximum	I_{Leak}	1μA (N.O.), 10μA (N.C.)		$I_F = 0$ mA (N.O.) $I_F = 5$ mA (N.C.) $V_L = Max.$	
Transfer characteristics	Operate (OFF) time*	Typical	$T_{on(N.O.)}$	1.0 ms (N.O.) 3.0 ms (N.C.)	0.5 ms (N.O.) 1.0 ms (N.C.)	0.5 ms (N.O.) 0.8 ms (N.C.)	$I_F = 0$ mA → 5 mA $I_L = Max.$
		Maximum	$T_{off(N.C.)}$	4.0 ms (N.O.) 10.0 ms (N.C.)	3.0 ms		
	Reverse (ON) time*	Typical	$T_{off(N.O.)}$	0.05ms (N.O.), 0.2ms (N.C.)	0.08ms (N.O.), 0.3ms (N.C.)	0.08ms (N.O.), 0.2ms (N.C.)	$I_F = 5$ mA → 0 mA $I_L = Max.$
		Maximum	$T_{on(N.C.)}$	1.0ms			
	I/O capacitance	Typical	C_{iso}	0.8 pF			f = 1MHz $V_B = 0$ V
	Maximum	1.5 pF					
	Initial I/O isolation resistance	Minimum	R_{iso}	1,000MΩ		500 V DC	

Note: Recommendable LED forward current $I_F = 5$ to 10 mA.

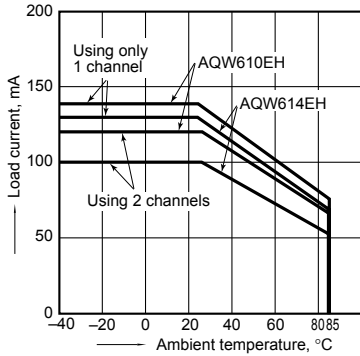
*Operate/Reverse time



REFERENCE DATA

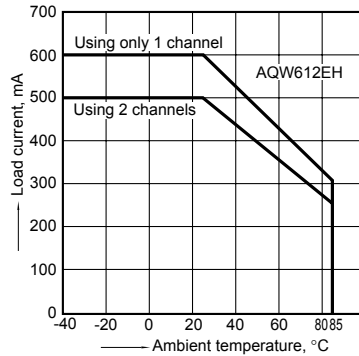
1-(1). Load current vs. ambient temperature characteristics

Allowable ambient temperature: -40°C to $+85^{\circ}\text{C}$
 -40°F to $+185^{\circ}\text{F}$



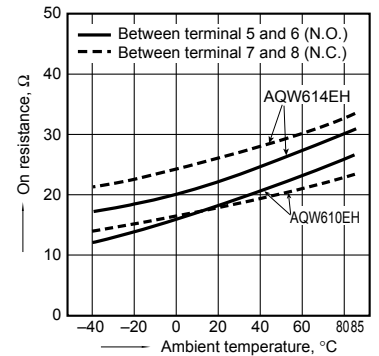
1-(2). Load current vs. ambient temperature characteristics

Allowable ambient temperature: -40°C to $+85^{\circ}\text{C}$
 -40°F to $+185^{\circ}\text{F}$



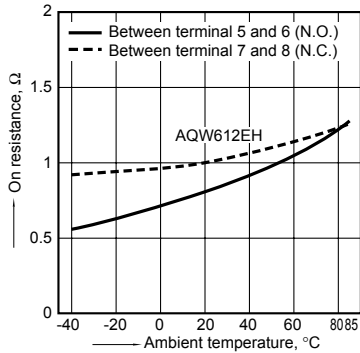
2-(1). On resistance vs. ambient temperature characteristics

Measured portion: between terminals 5 and 6, 7 and 8;
 LED current: 5 mA; Load voltage: Max. (DC)
 Continuous load current: Max. (DC)



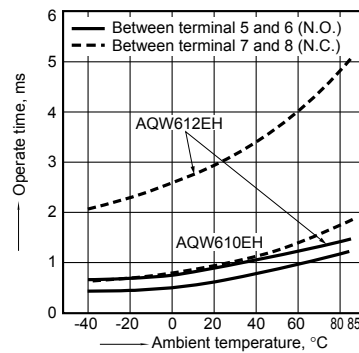
2-(2). On resistance vs. ambient temperature characteristics

Measured portion: between terminals 5 and 6, 7 and 8;
 LED current: 5 mA; Load voltage: Max. (DC)
 Continuous load current: Max. (DC)



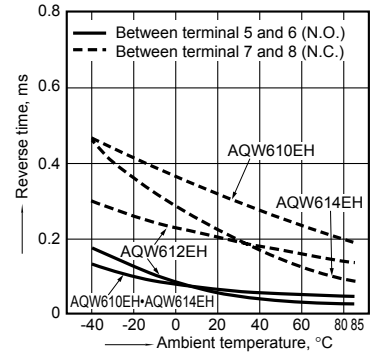
3. Operate time vs. ambient temperature characteristics

LED current: 5 mA; Load voltage: Max. (DC);
 Continuous load current: Max. (DC)



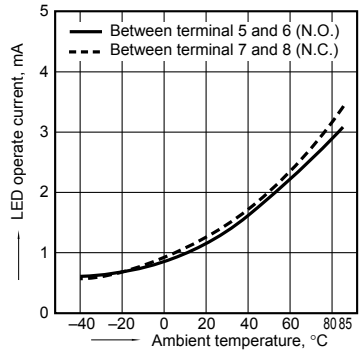
4. Reverse time vs. ambient temperature characteristics

LED current: 5 mA; Load voltage: Max. (DC);
 Continuous load current: Max. (DC)



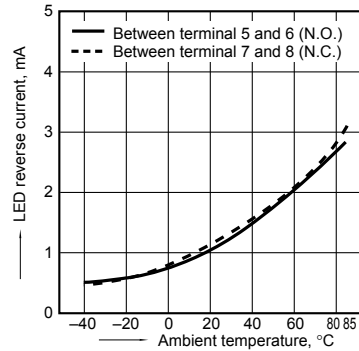
5. LED operate current vs. ambient temperature characteristics

Sample: All types;
 Load voltage: Max. (DC);
 Continuous load current: Max. (DC)



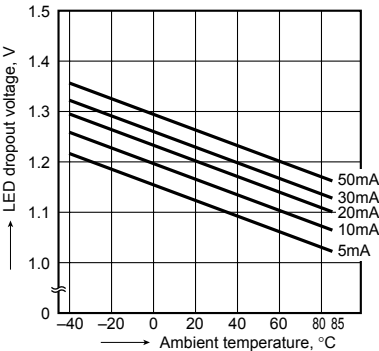
6. LED reverse current vs. ambient temperature characteristics

Sample: All types;
 Load voltage: Max. (DC);
 Continuous load current: Max. (DC)



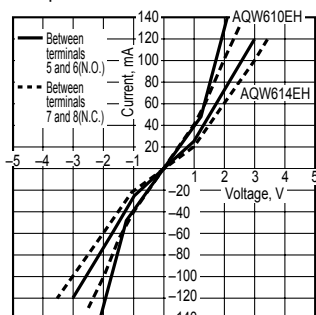
7. LED dropout voltage vs. ambient temperature characteristics

Sample: All types;
 LED current: 5 to 50 mA



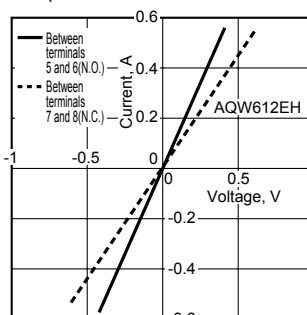
8-(1). Current vs. voltage characteristics of output at MOS portion

Measured portion: between terminals 5 and 6, 7 and 8;
 Ambient temperature: 25°C 77°F



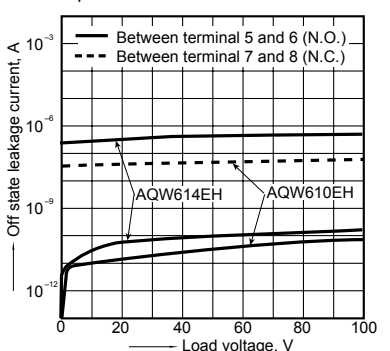
8-(2). Current vs. voltage characteristics of output at MOS portion

Measured portion: between terminals 5 and 6, 7 and 8;
 Ambient temperature: 25°C 77°F



9-(1). Off state leakage current vs. load voltage characteristics

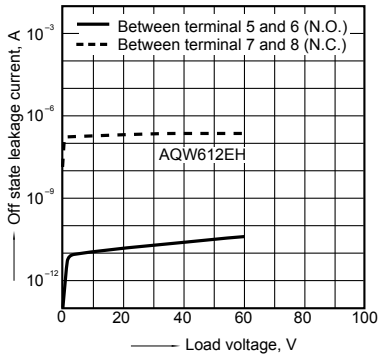
Measured portion: between terminals 5 and 6, 7 and 8;
 Ambient temperature: 25°C 77°F



GU-E PhotoMOS (AQW610EH)

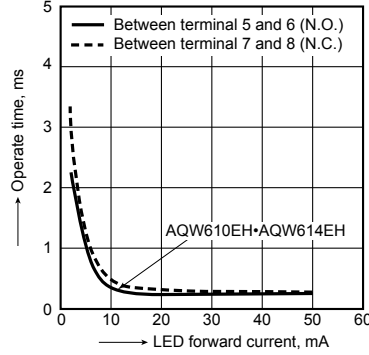
9-(2). Off state leakage current vs. load voltage characteristics

Measured portion: between terminals 5 and 6, 7 and 8;
Ambient temperature: 25°C 77°F



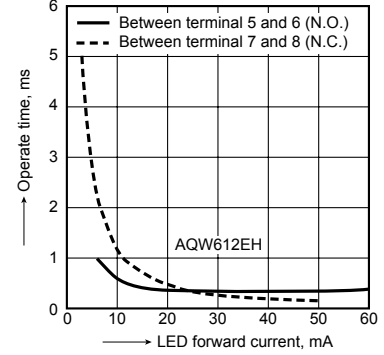
10-(1). Operate time vs. LED forward current characteristics

Measured portion: between terminals 5 and 6, 7 and 8;
Load voltage: Max. (DC); Continuous load current: Max. (DC); Ambient temperature: 25°C 77°F



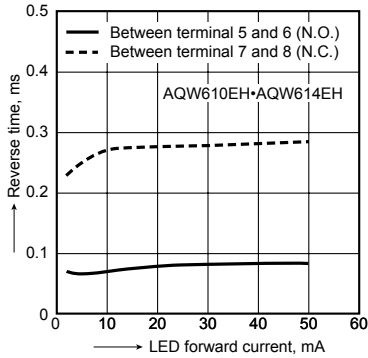
10-(2). Operate time vs. LED forward current characteristics

Measured portion: between terminals 5 and 6, 7 and 8;
Load voltage: Max. (DC); Continuous load current: Max. (DC); Ambient temperature: 25°C 77°F



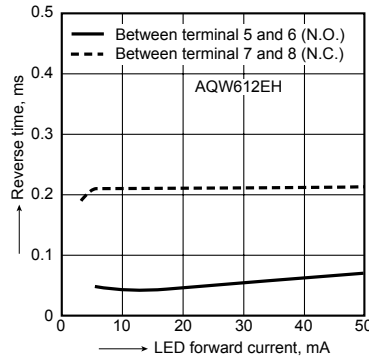
11-(1). Reverse time vs. LED forward current characteristics

Measured portion: between terminals 5 and 6, 7 and 8;
Load voltage: Max. (DC); Continuous load current: Max. (DC); Ambient temperature: 25°C 77°F



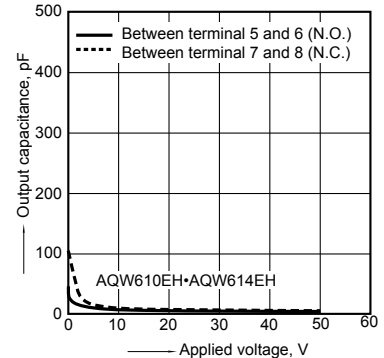
11-(2). Reverse time vs. LED forward current characteristics

Measured portion: between terminals 5 and 6, 7 and 8;
Load voltage: Max. (DC); Continuous load current: Max. (DC); Ambient temperature: 25°C 77°F



12-(1). Output capacitance vs. applied voltage characteristics

Measured portion: between terminals 5 and 6, 7 and 8;
Frequency: 1 MHz;
Ambient temperature: 25°C 77°F



12-(2). Output capacitance vs. applied voltage characteristics

Measured portion: between terminals 5 and 6, 7 and 8;
Frequency: 1 MHz;
Ambient temperature: 25°C 77°F

